-500mA / -40V Digital transistors (with built-in resistor)

DTB143TK

Applications

Inverter, Interface, Driver

Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on / off conditions need to be set for operation, making the device design easy.

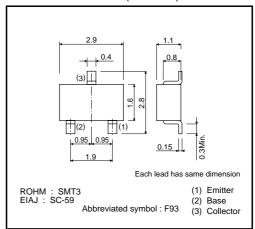
Structure

PNP epitaxial planar silicon transistor (Resistor built-in type)

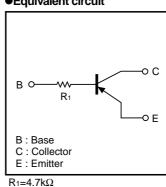
Packaging specifications

| | Package | SMT3 | | | |
|----------|------------------------------|--------|--|--|--|
| | Packaging type | Taping | | | |
| | Code | T146 | | | |
| Part No. | Basic ordering unit (pieces) | 3000 | | | |
| DTB143TK | | 0 | | | |
| | | | | | |

●External dimensions (Unit : mm)



●Equivalent circuit



● Absolute maximum ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit |
|-----------------------------|--------|-------------|------|
| Collector-base voltage | Vсво | -50 | V |
| Collector-emitter voltage | Vceo | -40 | V |
| Emitter-base voltage | Vево | -5 | V |
| Collector current | Ic | -500 | mA |
| Collector power dissipation | Pc | 200 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

●Electrical characteristics (Ta=25°C)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|--------------------------------------|----------------|------|------|------|------|----------------------------------|
| Collector-base breakdown voltage | ВУсво | -50 | _ | _ | V | Ic=-50μA |
| Collector-emitter breakdown voltage | BVceo | -40 | _ | _ | V | Ic=-1mA |
| Emitter-base breakdown voltage | ВУево | -5 | _ | _ | V | I _E = -50μA |
| Collector cutoff current | Ісво | _ | _ | -0.5 | μΑ | Vcb= -50V |
| Emitter cutoff current | ІЕВО | _ | _ | -0.5 | μА | V _{EB} = -4V |
| Collector-emitter saturation voltage | VCE(sat) | _ | _ | -0.3 | V | Ic/I _B = -50mA/-2.5mA |
| DC current transfer ratio | hfe | 100 | 250 | 600 | _ | Vce= -5V, Ic= -50mA |
| Input resistance | R ₁ | 3.29 | 4.7 | 6.11 | kΩ | - |
| Transition frequency | f ⊤ ∗ | _ | 200 | _ | MHz | Vc==-10V, Ie=50mA, f=100MHz |

^{*} Characteristics of built-in transistor

•Electrical characteristic curves

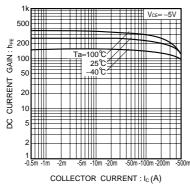


Fig.1 DC current gain vs. collectorcurrent

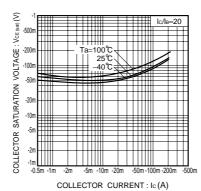


Fig.2Collector-emitter saturation voltage vs. collector current

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